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ABSTRACT

The present invention relates to a method for producing a silicon wafer, wherein the method comprises at least a lapping process by use of loose abrasive grains and an etching process by use of an alkaline etching solution, lapping is performed in the lapping process by use of abrasive grains having a maximum grain diameter of 21 μm or less and an average grain diameter of 8.5 μm or less serving as the loose abrasive grains, and after that, etching is performed in the etching process by use of an alkaline solution having a concentration of an alkaline component of 50% by weight or more serving as the alkaline etching solution, and relates to a silicon wafer produced by the production method. Thus, there can be provided a method for producing a silicon wafer which can prevent degradation of surface roughness of the wafer and flatness of the whole wafer, and a silicon wafer produced by the method.



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